

" &ROOHFWRU &XUUHQW &DSDELWLW\ ,& \$
 " &ROOHFWRU (PLWWHU 9ROWDJH 9&(2 9
 " /RZ)UHTXHQF\ 3RZHU \$PSOLILHU \$SSOLFDWLRQ
 " 3RZHU 6ZLWKLQJ \$SSOLFDWLRQV

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-35	V
Collector - Emitter Voltage	V _{CEO}	-30	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-800	mA
Collector Power Dissipation	P _C	200	mW
Thermal Resistance From Junction To Ambient	R _{JA}	625	/W
Junction Temperature	T _J	150	
Storage Temperature range	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -1mA ÷ I _E =0	-35			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA ÷ I _B =0	-30			
Emitter - base breakdown voltage	V _{EB0}	I _E = -1mA ÷ I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -30 V , I _E =0			-0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V , I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-20mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B =-20mA			-1.2	
Base - emitter voltage	V _{BE}	V _{CE} =-1V, I _C = -10 mA			-0.8	
DC current gain	h _{FE(1)}	V _{CE} = -1V, I _C = -100mA	100		320	
	h _{FE(2)}	V _{CE} =- 1V, I _C = -800mA	40			
Collector output capacitance	C _{ob}	V _{CB} = -6V, I _E = 0, f=1MHz		13		pF
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA		120		MHz

μ Classification of h_{FE(1)}

μ Typical Characteristics